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## Editor's note

This issue of the *IBM Journal of Research and Development* comprises the Proceedings of the Symposium on Instabilities in Semiconductors. This symposium, sponsored jointly by the American Physical Society and IBM, was held on March 20 and 21, 1969, at the Thomas J. Watson Research Center in Yorktown Heights, New York.

The organizing committee for this topical conference consisted of D. J. Bartelink, Ralph Bray, E. M. Conwell, Maureen Glicksman, J. B. Gunn, G. S. Kino, Murray Lampert, M. I. Nathan, and R. A. Stratton.

The four half-day sessions in the program included the following general subjects: (1) acoustoelectric effects; (2) general instabilities, including bulk and surface phenomena; (3) bulk negative differential conductivity; and (4) microwave instabilities. Ten invited and 24 contributed papers were presented. These Proceedings include the invited papers and 16 of the contributed papers. The papers appear in these Proceedings in the order in which they were presented in the program.

The eight contributed papers which were not submitted for publication with the Proceedings are listed below by title and author.

Acoustoelectric Surface Wave Interactions between Silicon and Lithium Niobate, by G. S. Kino, T. M. Reeder, and R. M. Lakin.

Coherent Microwave Radiation from BiSb Alloys, by C. S. Nanney and E. V. George.

An Explanation of Impact Ionization in InSb, by C. L. Dick and B. Ancker-Johnson.

Transverse Electromagnetic Wave Amplification in n-GaAs, by B. R. Chawla, D. J. Bartelink and D. J. Coleman.

Fast Space-Charge Waves in Negative Mobility Semiconductors, by H. W. Thim.

Surface Wavelength Measurements of Microwave Emission from InSb, by D. A. Platts and A. Bers.

The Effect of Contacts on the Low-field RF Emission from InEb, by E. V. George and G. Bekefi.

The Relationship between Microwave Emission from InSb with and without a Magnetic Field, by B. Ancker-Johnson.

Abstracts of all the papers have appeared in the Bulletin of the American Physical Society, Series II, 14, No. 6, 744-50 (June 1969).